Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				60	
I_H	I_T =100mA		MAX.	35	mA
dV/dt	V_D=540V Gate Open T_j =150		MIN.	1200	V s
(dI/dt)c	$_j$=150		MIN.	8	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	s
t_{off}				30	

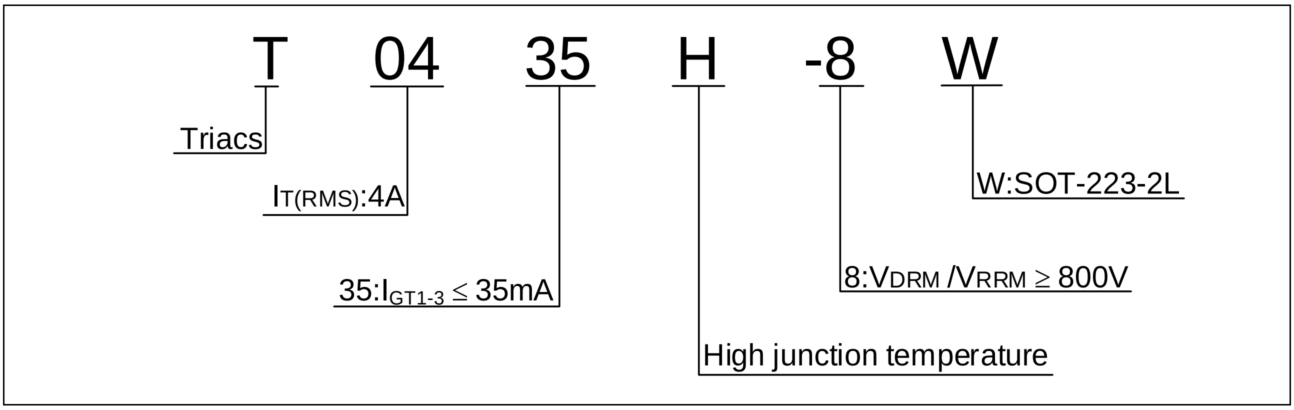
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =5A t_p=380 s	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=150	0.63	V
R_D	Dynamic resistance	T_j=150	324	m
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=150	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	17	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING

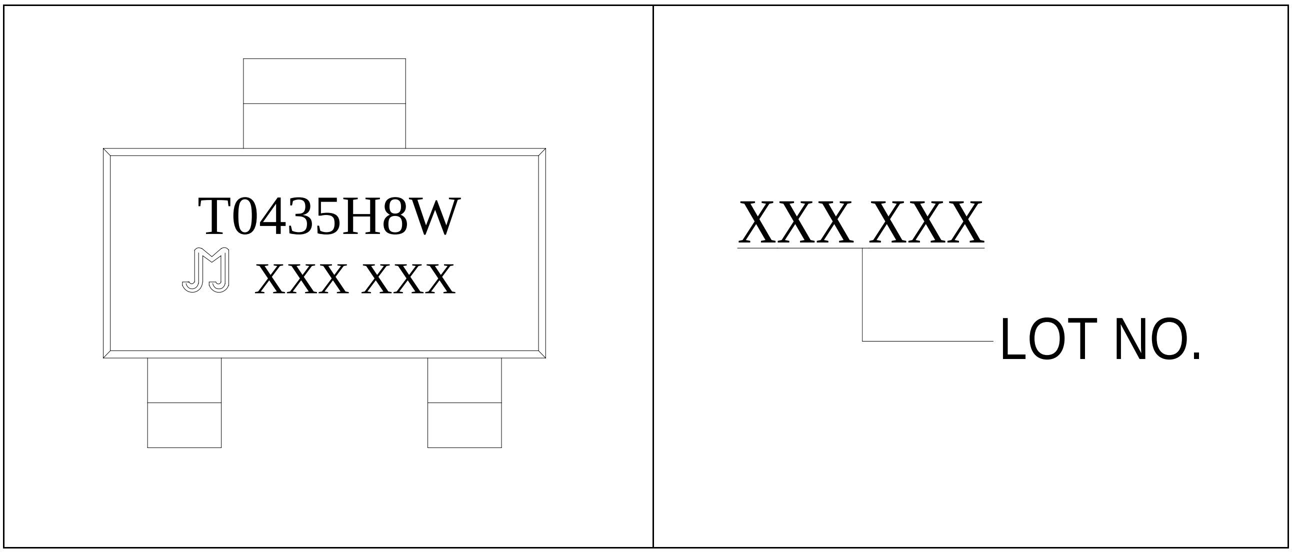


FIG.1: Maximum power dissipation versus RMS on-state current

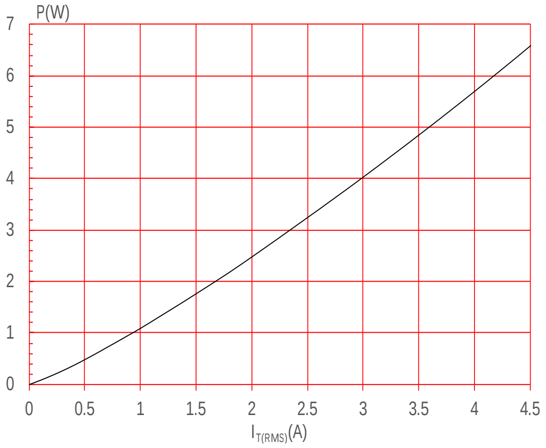


FIG.2: RMS on-state current versus case temperature

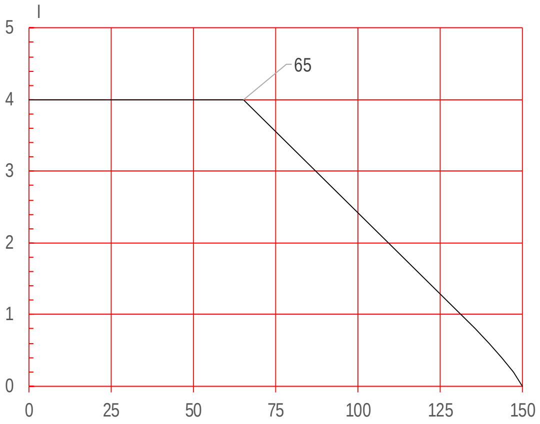
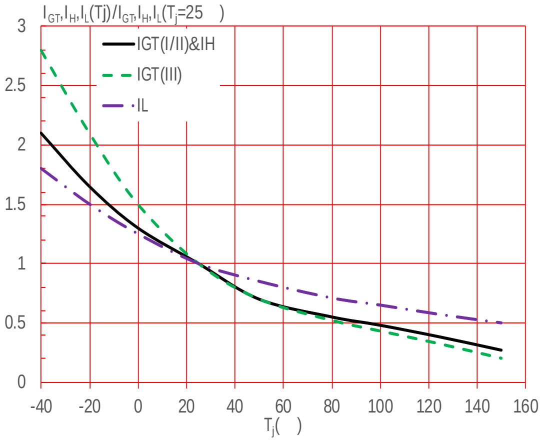


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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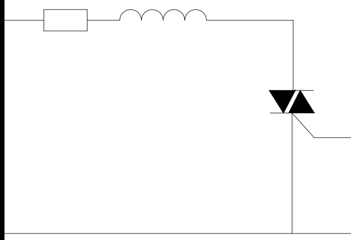
oads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA